



## SEMI® INTERNATIONAL STANDARDS

# Edge Profiling as part of an overall strategy for edge inspection and metrology in IC Fabs

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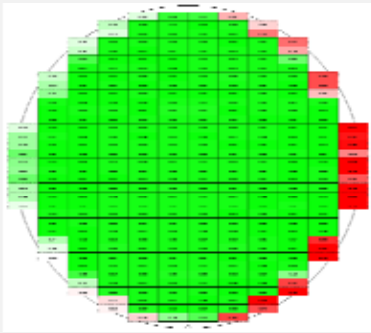
# Summary

- Edge is becoming “Prime Time” yield focus at 300mm IC manufacturers
- Not simply defect inspection
  - Defect Inspection + Edge Metrology + Edge Profile
- Edge Profiler (EP) use cases:
  - Litho z-cut (production)
  - Defect/EP correlation, IQC, packaging (enr/dev)

# Process control shift toward the wafer edge

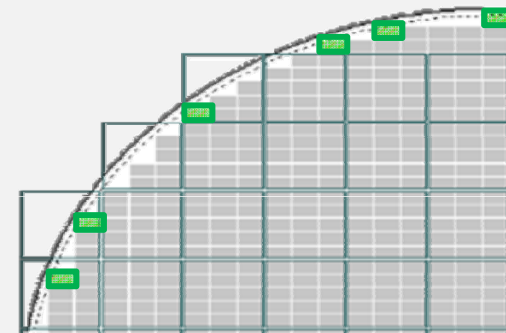
## Improving Edge Yield

*Lowest yields traditionally at wafer edge*



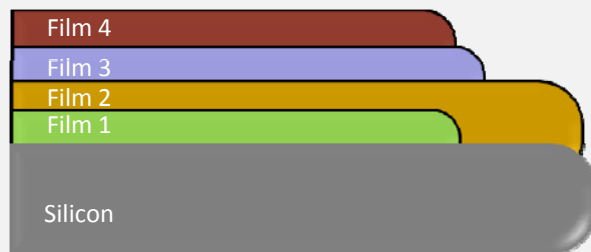
## Decreasing Wafer Edge Exclusion

*Increase real estate for sellable product*



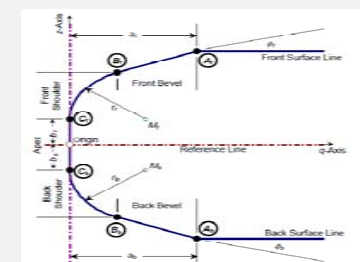
## Film Edge Stack Complexity

*More films; Smaller width tolerances*



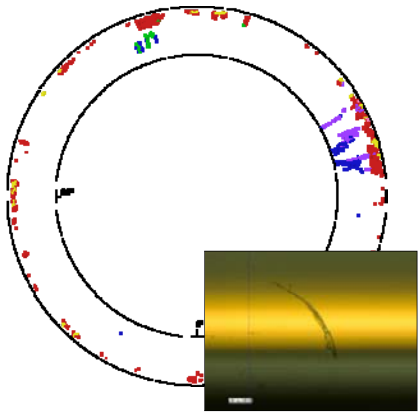
## Need for Edge Profile Control

*Incoming quality control, iLitho bevel film position (z-cut)*



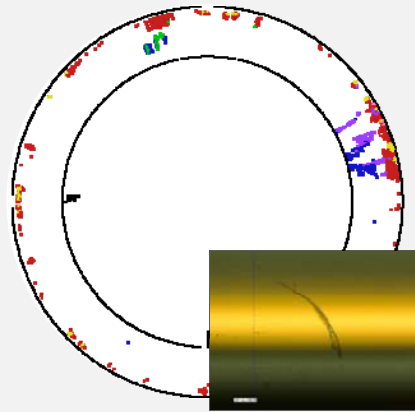
# Evolving Edge Process Control Requirements

65nm & 45nm  
processes

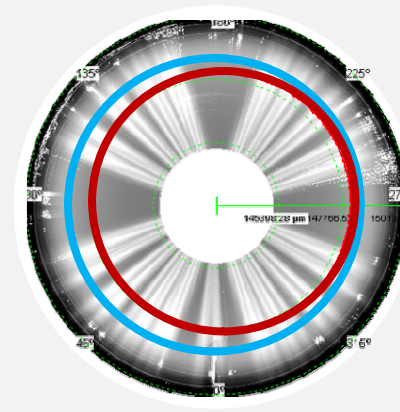


Edge Defect  
Detection & Review

32nm, 28nm, 22nm, iLitho....



Edge Defect  
Detection & Review

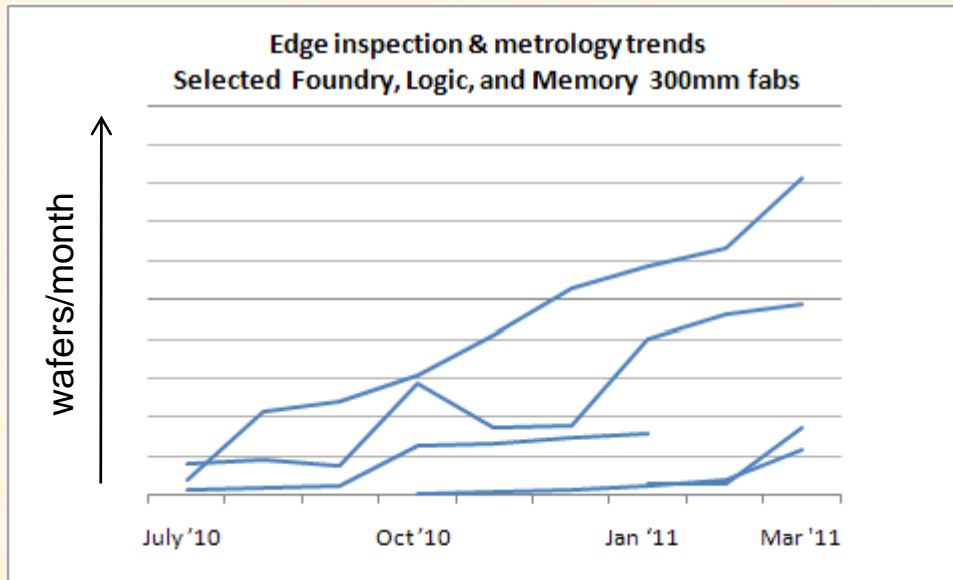


Film Concentricity  
Metrology



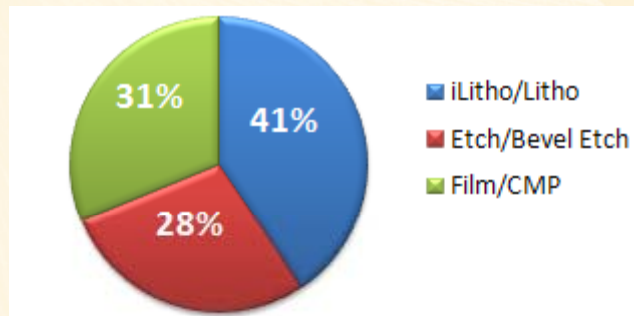
Edge Profile &  
Film z-height

# Wafer Edge Inspection is Increasing

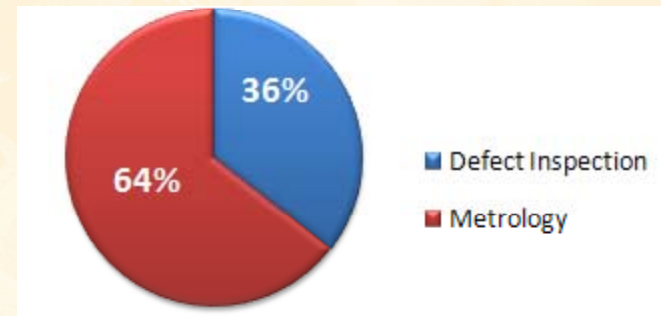


VisEdge CV300R-EP

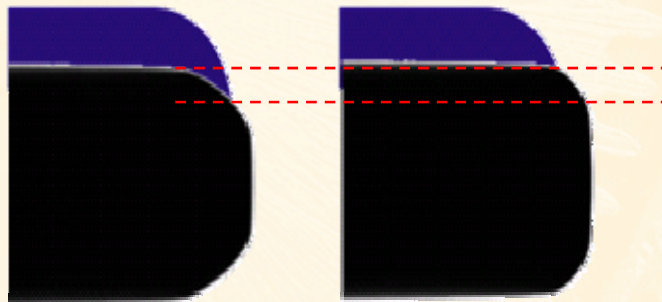
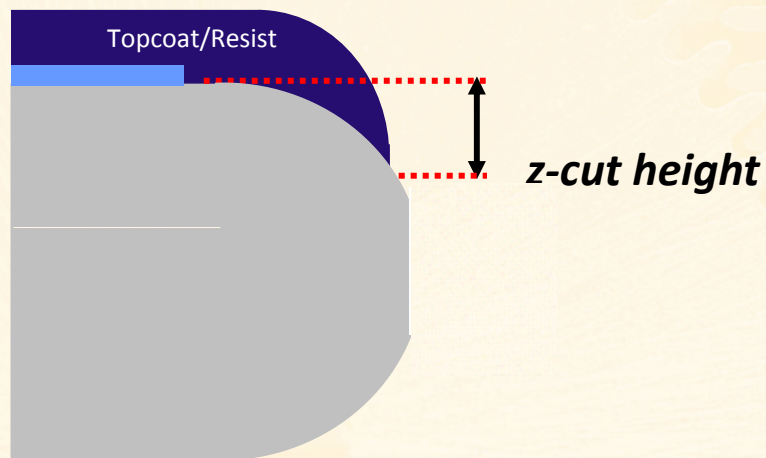
Edge Applications



Production Use Cases



# Immersion Litho Edge Metrology Monitoring



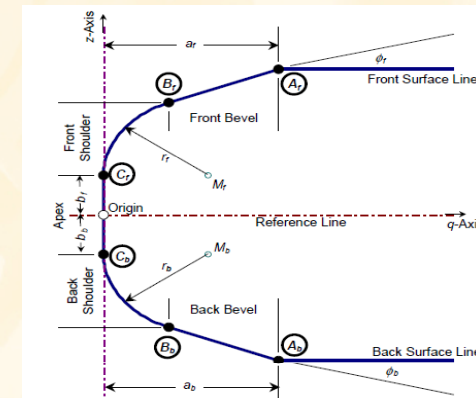
- z-cut height control
  - Film too high on bevel → risk **water leakage**
  - Film too low on bevel → risk **film de-lamination**
- Loss of meniscus @ scanner → risk **fouling bath**
- Accurate z-cut measurement requires integrated Edge Profile correction

# Edge Profiler & SEMI Model

## Edge Attribute Description (SEMI M73)

Wafer thickness, $t$ ( $\mu\text{m}$ ) <sup>#1</sup>	Segment Parameters	Symbol	Unit	Explanation
Edge Width, $a_f$ or $a_b$ ( $\mu\text{m}$ ) <sup>#2</sup>	Front Bevel Angle	$\phi_f$	$^\circ$	Angle between front surface and front bevel, taken as positive into the wafer.
	Front Shoulder Radius	$r_f$	$\mu\text{m}$	Radius of the arc of the front shoulder.
	Front Apex Length	$b_f$	$\mu\text{m}$	Distance from origin to the beginning of the front shoulder arc.
	Front Apex Angle	$\beta_f$	$^\circ$	Angle between z-axis and front apex, taken as positive in the +q direction
	Back Apex Angle	$\beta_b$	$^\circ$	Angle between z-axis and back apex, taken as positive in the +q direction.
	Back Apex Length	$b_b$	$\mu\text{m}$	Distance from origin to the beginning of the back shoulder arc.
	Back Shoulder Radius	$r_b$	$\mu\text{m}$	Radius of the arc of the back shoulder.
	Back Bevel Angle	$\phi_b$	$^\circ$	Angle of the back surface and back bevel, taken as positive into the wafer.

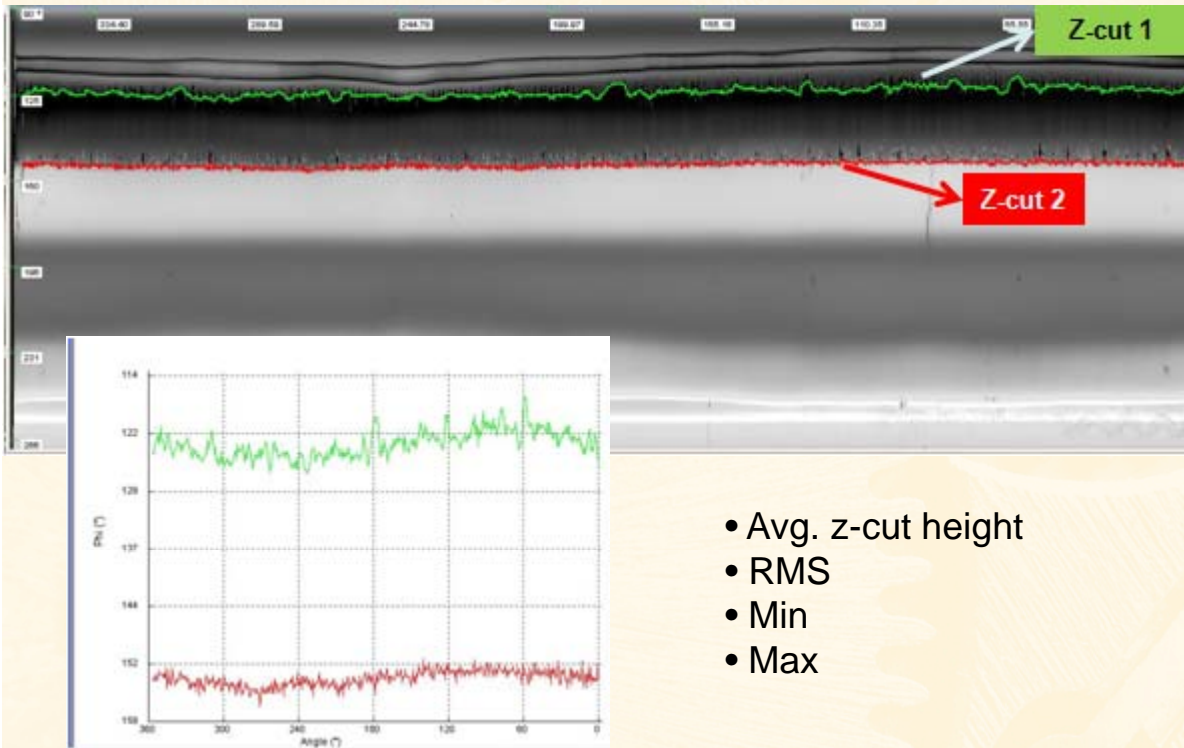
## SEMI M73 Model



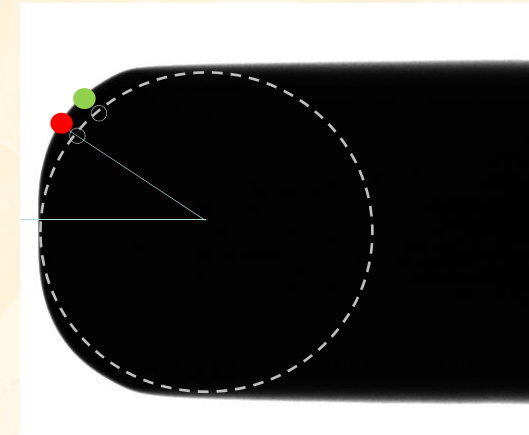
VisEdge CV300R-EP integrates Edge Profiler measurements into EBR position measurement algorithms

# iLitho Resist + BARC z-cut - Example

Scan Image



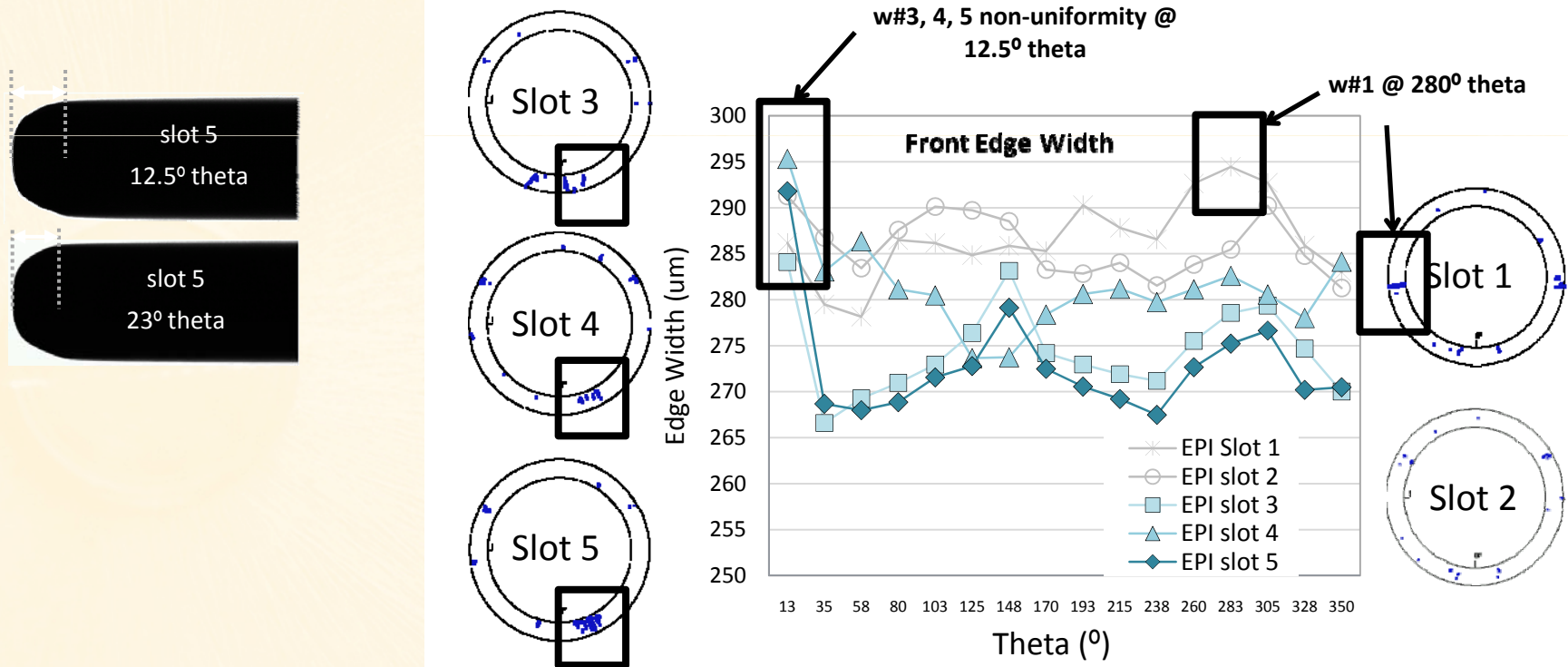
- Avg. z-cut height
- RMS
- Min
- Max



EBR metrology + Edge Profile correction for accurate z-cut height

# Edge Profile & Edge Defectivity

Edge Scratch signatures



Investigating influence of EP shape on edge process defectivity

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# VisEdge CV300R-EP

## Performance Leadership in Edge Inspection & Metrology

- Comprehensive edge control system: defect inspection, film metrology & wafer profiling
- Full edge zone coverage
- Patterned area algorithms for edge and partial die
- Integrated Edge Profiler



# VisEdge CV300R-EP

Control the Edge....Raise the Yield

**THANK YOU**